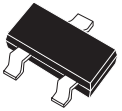
CMPD4150

HIGH CURRENT
HIGH SPEED
SWITCHING DIODE



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD4150 type is an ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.
Marking code is ABA.

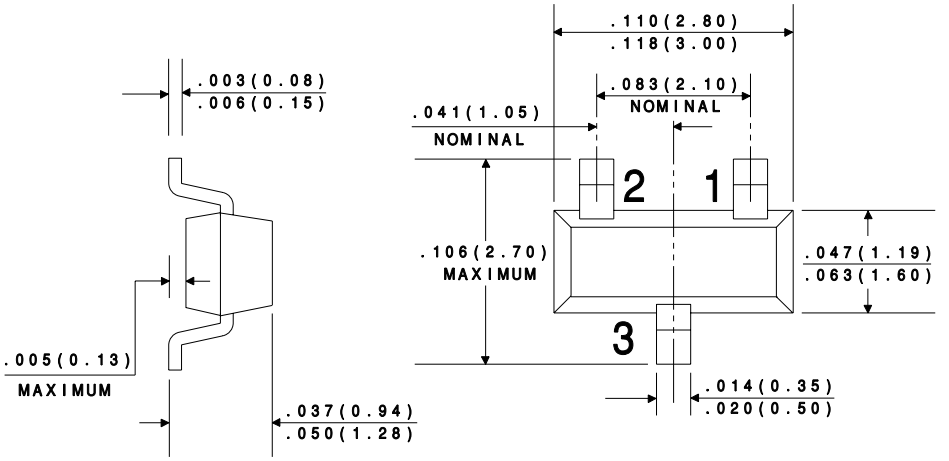
MAXIMUM RATINGS (T_A=25°C)

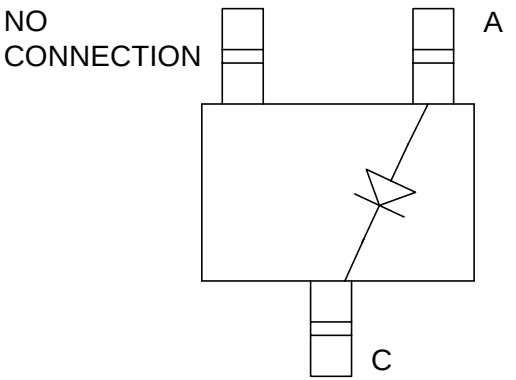
	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	50	V
Peak Repetitive Reverse Voltage	V_{RRM}	50	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, tp=1 μsec.	I_{FSM}	4000	mA
Forward Surge Current, tp=1 sec.	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	V_R=50V		100	nA
V_F	I_F=1.0mA	0.54	0.62	V
V_F	I_F=10mA	0.66	0.74	V
V_F	I_F=50mA	0.76	0.86	V
V_F	I_F=100mA	0.82	0.92	V
V_F	I_F=200mA	0.87	1.0	V
C_T	V_R=0, f=1 MHz		4.0	pF
t_{rr}	I_R=I_F=10mA, R_L=100Ω, Rec. to 1.0mA		4.0	ns

All dimensions in inches (mm).





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